

## NPN DARLINGTON POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/502

### Devices

2N6058

2N6059

### Qualified Level

JANTX  
JANTXV

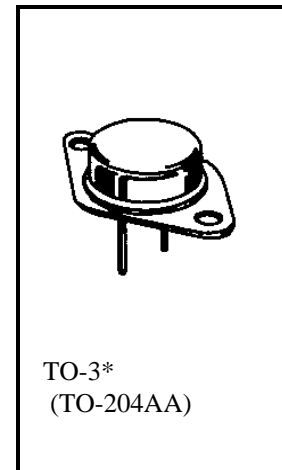
### MAXIMUM RATINGS

Ratings	Symbol	2N6058	2N6059	Units
Collector-Emitter Voltage	$V_{CEO}$	80	100	Vdc
Collector-Base Voltage	$V_{CBO}$	80	100	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0		Vdc
Base Current	$I_B$	0.2		Adc
Collector Current	$I_C$	12		Adc
Total Power Dissipation <sup>(1)</sup>	$P_T$	@ $T_C = +25^{\circ}C$	150	W
		@ $T_C = +100^{\circ}C$	75	W
Operating & Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +175		$^{\circ}C$

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	$^{\circ}C/W$

1) Derate linearly at 1.0 W/ $^{\circ}C$  above  $T_C > +25^{\circ}C$



\*See appendix A for package outline

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 100$ mAdc	2N6058 2N6059	$V_{(BR)CEO}$	80 100	Vdc
Collector-Emitter Cutoff Current $V_{CE} = 40$ Vdc $V_{CE} = 50$ Vdc	2N6058 2N6059	$I_{CEO}$	1.0 1.0	mAdc
Collector-Emitter Cutoff Current $V_{CE} = 80$ Vdc, $V_{BE} = 1.5$ Vdc $V_{CE} = 100$ Vdc, $V_{BE} = 1.5$ Vdc	2N6058 2N6059	$I_{CEX}$	0.5 0.5	mAdc
Emitter-Base Cutoff Current $V_{EB} = 5.0$ Vdc		$I_{EBO}$	2.0	mAdc

